



N-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY								
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A) ^a	Q _g (Typ.)					
12	0.0198 at V _{GS} = 4.5 V	4.5						
	0.0222 at V _{GS} = 2.5 V	4.5	13.7 nC					
	0.0264 at V _{GS} = 1.8 V	4.5						

FEATURES

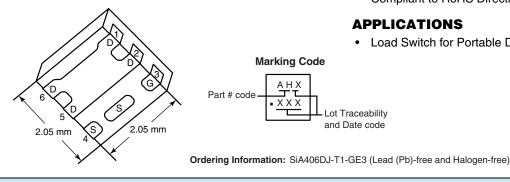
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- 100 % R_q Tested

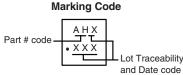
APPLICATIONS

Compliant to RoHS Directive 2002/95/EC

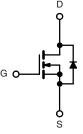








· Load Switch for Portable Devices



N-Channel MOSFET

Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V_{DS}	12	V		
Gate-Source Voltage		V_{GS}	± 8	v		
	T _C = 25 °C		4.5 ^a			
Continuous Drain Current (T _{.I} = 150 °C) ^a	T _C = 70 °C	I_	4.5 ^a			
Continuous Drain Current (1) = 150 °C)	T _A = 25 °C	I _D	4.5 ^{a, b, c}			
	T _A = 70 °C		4.5 ^{a, b, c}	A		
Pulsed Drain Current		I _{DM}	20			
Continuous Source-Drain Diode Current	T _C = 25 °C	I_	4.5 ^a			
Continuous Source-Diam Diode Current	T _A = 25 °C	I _S	2.9 ^{b, c}			
	T _C = 25 °C		19			
Maximum Power Dissipation	T _C = 70 °C	P _D	12	□ w		
Maximum Fower Dissipation	T _A = 25 °C	' 0	3.5 ^{b, c}			
	T _A = 70 °C		2.2 ^{b, c}			
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature	e) ^{d, e}		260			

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	5.3	6.5]				

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

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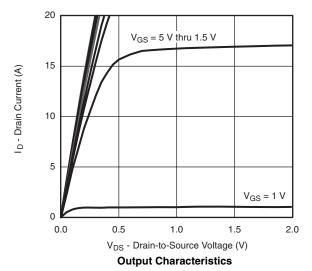
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static					L	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$	12			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050A		11		mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 2.9		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	0.4		1.0	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA
		$V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$		20		Α
	` ,	$V_{GS} = 4.5 \text{ V}, I_D = 10.8 \text{ A}$		0.0165	0.0198	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 10.2 A		0.0185	0.0222	
	= = (=,	V _{GS} = 1.8 V, I _D = 3 A		0.0220	0.0264	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 6 V, I _D = 10.8 A		38		S
Dynamic ^b						<u> </u>
Input Capacitance	C _{iss}			1380		
Output Capacitance	C _{oss}	V _{DS} = 6 V, V _{GS} = 0 V, f = 1 MHz		345		pF
Reverse Transfer Capacitance	C _{rss}	D3 - 7 G3 - 7		155		
Tievelee Transler Supusitation		V _{DS} = 6 V, V _{GS} = 5 V, I _D = 10.8 A		15.2	23	nC
Total Gate Charge	Q_g	103 1 17 1G3 1 17 1D 1010 11		13.7	21	
Gate-Source Charge	Q _{gs}	V _{DS} = 6 V, V _{GS} = 4.5 V, I _D = 10.8 A		2.6		
Gate-Drain Charge	Q _{gd}	26 · GC · D		1.1		
Gate Resistance	R _q	f = 1 MHz	0.5	2.5	5	Ω
Turn-On Delay Time	t _{d(on)}			10	20	
Rise Time	t _r	$V_{DD} = 6 \text{ V}, R_1 = 0.7 \Omega$		9	18	- - -
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 8.6 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_q = 1 \Omega$		40	60	
Fall Time	t _f	Ű		14	21	
Turn-On Delay Time	t _{d(on)}			6	12	ns
Rise Time	t _r	$V_{DD} = 6 \text{ V}, R_1 = 0.7 \Omega$		11	17	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 8.6 \text{ A}, V_{GEN} = 8 \text{ V}, R_q = 1 \Omega$		27	41	
Fall Time	t _f	- 3		9	18	
Drain-Source Body Diode Characterist]
Continuous Source-Drain Diode Current	Is	T _C = 25 °C			4.5 ^c	
Pulse Diode Forward Current	I _{SM}				20	- A
Body Diode Voltage	V _{SD}	I _S = 8.6 A, V _{GS} = 0 V		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	-		22	33	ns
Body Diode Reverse Recovery Charge	Q _{rr}			7	14	nC
Reverse Recovery Fall Time	t _a	$I_F = 8.6 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		8		ns
Reverse Recovery Rise Time	t _b			14		

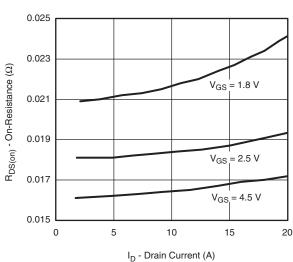
- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Package limited

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

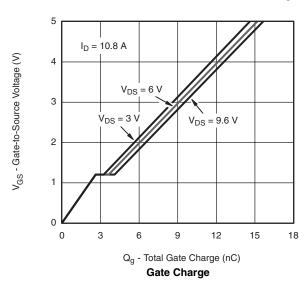


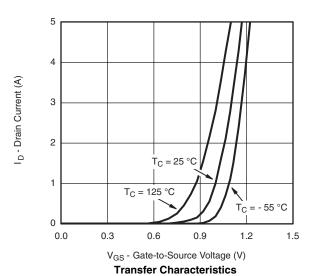
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

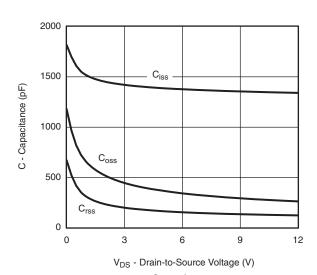


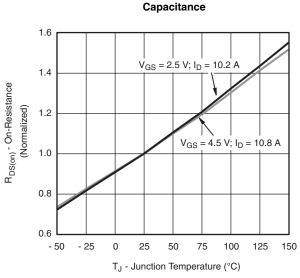


On-Resistance vs. Drain Current and Gate Voltage









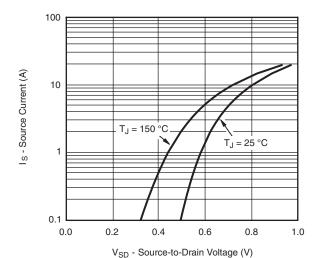
On-Resistance vs. Junction Temperature

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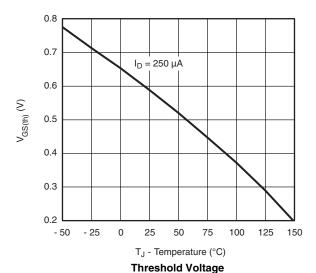
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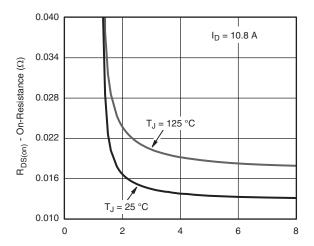
VISHAY.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



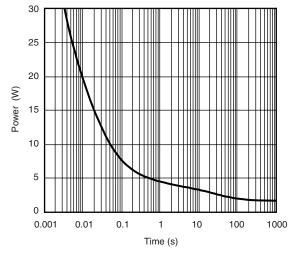
Soure-Drain Diode Forward Voltage



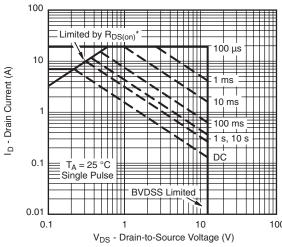


V_{GS} - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

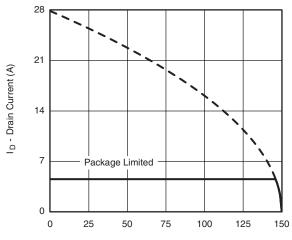


* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

Safe Operating Area, Junction-to-Ambient

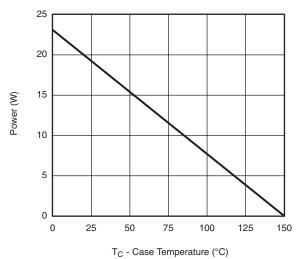


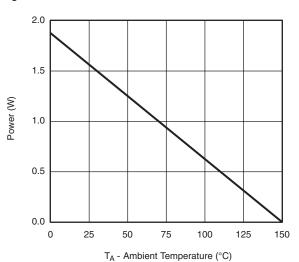
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



T_C - Case Temperature (°C)

Current Derating*





Power, Junction-to-Ambient

Power, Junction-to-Case

EO °C using junction to cope thermal registance, and is more useful in cettling the upper

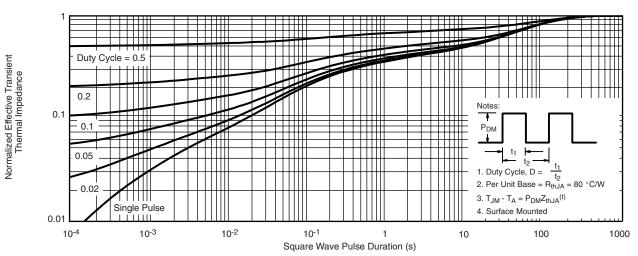
^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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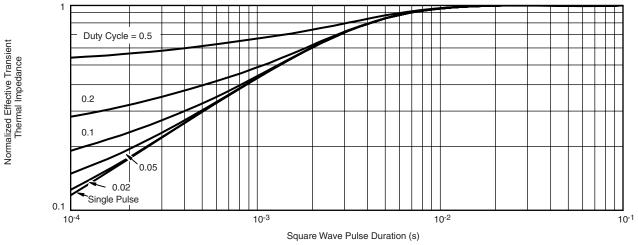
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65361.





PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP 0.011 TYP		0.275 TYP			0.011 TYP					
K1		0.400 TYP 0.016 TYP		0.320 TYP			0.013 TYP					
K2		0.240 TYP 0.009 TYP		0.252 TYP			0.010 TYP					
К3	0.225 TYP 0.009 TYP				•		•	•				
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT





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